

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

**Claims 1 - 17 (Canceled).**

18. (New) A semiconductor integrated circuit device for receiving operation of a mobile radio communication apparatus comprising:

    a sealing package enclosing a semiconductor chip and having four sides and being formed in rectangular shape in a plane view;

    a first low noise amplifier into which a radio frequency reception signal of a first frequency band is to be inputted;

    a second low noise amplifier into which a radio frequency reception signal of a second frequency band is to be inputted, the second frequency band being different from the first frequency band;

    another circuit;

    a first receiving mixer for the first frequency band into which an output signal from said first low noise amplifier is to be inputted;

    a second receiving mixer for the second frequency band into which an output signal from said second low noise amplifier is to be inputted;

    a first pad disposed on said semiconductor chip and electrically connected to said first low noise amplifier;

    a second pad disposed on said semiconductor chip and electrically connected to said second low noise amplifier;

    a third pad disposed on said semiconductor chip and electrically connected to

said another circuit;

    a first input pin having a first pin end projecting to outside said sealing package and electrically connected to said first pad;

    a second input pin having a second pin end projecting to outside at the same side of said sealing package where the first pin end is projecting to outside and electrically connected to said second pad; and

    another pin having a third pin end projecting to outside at the same side of said sealing package where the first pin end is projecting to outside and electrically connected to said third pad,

    wherein said first and second low noise amplifiers, said another circuit, said first and second receiving mixers, said first, second, and third pads, said first and second input pins, and said another pin are monolithically integrated on the semiconductor chip,

    wherein said first and second pads are disposed at the same one of four sides of the semiconductor chip,

    wherein a distance between said first pad and said first pin end and a distance between said second pad and said second pin end are shorter than a distance between said third pad and said third pin end, and

    wherein said radio frequency reception signal of the first frequency band is to be applied to said first input pin and said radio frequency reception signal of the second frequency band is to be applied to said second input pin.

19. (New)    The semiconductor integrated circuit device according to claim 18,

    wherein said first receiving mixer is provided so as to receive a local

oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band. \

20. (New) The semiconductor integrated circuit device according to claim 18, further comprising:

a first output pin electrically connected to said first low noise amplifier; and  
a second output pin electrically connected to said second low noise amplifier,  
wherein a radio frequency reception signal of the first frequency band  
amplified through said first low noise amplifier is outputted from said first output pin  
and a radio frequency reception signal of the second frequency band amplified  
through said second low noise amplifier is outputted from said second output pin.

21. (New) The semiconductor integrated circuit device according to claim 20,

wherein said first receiving mixer is provided so as to receive a local  
oscillation signal of the first frequency band and said second receiving mixer is  
provided so as to receive a local oscillation signal of the second frequency band.

22. (New) The semiconductor integrated circuit device according to claim 20,

wherein said first low noise amplifier comprises a first bipolar transistor  
having an emitter to which a ground voltage is to be applied, a base electrically  
connected to said first input pin, and a collector electrically connected to said first  
output pin, and

wherein said second low noise amplifier comprises a second bipolar

transistor having an emitter to which a ground voltage is to be applied, a base electrically connected to said second input pin, and a collector electrically connected to said second output pin.

23. (New) The semiconductor integrated circuit device according to claim 22,

wherein said first receiving mixer is provided so as to receive a local oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band.

24. (New) A semiconductor integrated circuit device for receiving operation of a mobile radio communication apparatus comprising:

    a sealing package enclosing a semiconductor chip and having four sides being formed in rectangular shape in a plane view;

    a first radio frequency input filter into which a radio frequency reception signal of a first frequency band is to be inputted;

    a second radio frequency input filter into which a radio frequency reception signal of a second frequency band is to be inputted, the second frequency band being different from the first frequency band;

    a first input pin electrically connected to said first radio frequency input filter; and

    a second input pin electrically connected to said second radio frequency input filter,

    wherein said first and second input pins are monolithically integrated on said semiconductor chip,

wherein said first and second radio frequency input pins are coupled with said first and second radio frequency input filters, respectively, at one of four sides of said semiconductor chip,

wherein said first and second radio frequency input pins are disposed at said one side, and

wherein said radio frequency reception signal of the first frequency band is to be applied to said first input pin and said radio frequency reception signal of the second frequency band is to be applied to said second input pin.

25. (New) A semiconductor integrated circuit device according to claim 24, further comprising:

a first low noise amplifier into which a radio frequency reception signal of the first frequency band is to be inputted;

a second low noise amplifier into which a radio frequency reception signal of the second frequency band is to be inputted;

another circuit;

a first receiving mixer for the first frequency band into which an output signal from the first low noise amplifier is to be inputted; and

a second receiving mixer for the second frequency band into which an output signal from the second low noise amplifier is to be inputted,

wherein said first and second low noise amplifiers, said another circuit, and said first and second receiving mixers are monolithically integrated on one semiconductor chip,

wherein a distance between a first pad electrically connected to said first low noise amplifier and a first pin end of one of said first and second radio frequency

input pins projecting to outside the sealing package and electrically connected to the first pad is shorter than a distance between a second pad electrically connected to said second low noise amplifier and a second pin end of the other of said first and second radio frequency input pins projecting to outside the sealing package at the same side where the first pin end is projecting to outside the sealing package and electrically connected to the second pad,

wherein a distance between the first pad electrically connected to said first low noise amplifier and the first pin end of the one of said first and second radio frequency input pins projecting to outside the sealing package and electrically connected to the first pad is shorter than a distance between a third pad electrically connected to said another circuit and a third pin end projecting to outside the sealing package at the same side where the first pin end is projecting to outside the sealing package and electrically connected to the third pad, and

wherein said radio frequency reception signal of the first frequency band is to be applied to the first input pin having the first pin end and said radio frequency reception signal of the second frequency band is to be applied to the second input pin having the second pin end.

26. (New) A semiconductor integrated circuit device according to claim 25, wherein said first receiving mixer is provided so as to receive a local oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band.

27. (New) A semiconductor integrated circuit device according to claim 25, further comprising:

a first output pin electrically connected to said first low noise amplifier; and  
a second output pin electrically connected to said second low noise amplifier,  
wherein a radio frequency reception signal of the first frequency band  
amplified through said first low noise amplifier is outputted from said first output pin  
and a radio frequency reception signal of the second frequency band amplified  
through said second low noise amplifier is outputted from said second output pin.

28. (New) A semiconductor integrated circuit device according to claim 27,  
wherein said first receiving mixer is provided so as to receive a local  
oscillation signal of the first frequency band and said second receiving mixer is  
provided so as to receive a local oscillation signal of the second frequency band.

29. (New) A semiconductor integrated circuit device according to claim 27,  
wherein said first low noise amplifier comprises a first bipolar transistor  
having an emitter to which a ground voltage is to be applied, a base electrically  
connected to said first input pin, and a collector electrically connected to said first  
output pin, and

wherein said second low noise amplifier comprises a second bipolar  
transistor having an emitter to which a ground voltage is to be applied, a base  
electrically connected to said second input pin, and a collector electrically connected  
to said second output pin.

30. (New) A semiconductor integrated circuit device according to claim 29, wherein said first receiving mixer is provided so as to receive a local oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band.

31. (New) A semiconductor integrated circuit device comprising:  
a first low noise amplifier into which a radio frequency reception signal of a first frequency band is to be inputted;  
a second low noise amplifier into which a radio frequency reception signal of a second frequency band is to be inputted, the second frequency band being different from the first frequency band;  
another circuit;  
a first receiving mixer for the first frequency band into which an output signal from the first low noise amplifier is to be inputted;  
a second receiving mixer for the second frequency band into which an output signal from the second low noise amplifier is to be inputted;  
a first input pin electrically connected to said first low noise amplifier, the radio frequency reception signal of the first frequency band to be applied to said first input pin;  
a second input pin electrically connected to said second low noise amplifier, the radio frequency reception signal of the second frequency band to be applied to said second input pin; and  
a third input pin electrically connected to said another circuit,  
wherein the first and second low noise amplifiers, said another circuit, and said first and second receiving mixers are monolithically integrated on one

semiconductor chip, and

wherein said first, second, and third input pins are disposed at a same side of a four-sided said semiconductor integrated circuit device, in a plane view.

32. (New) A semiconductor integrated circuit device according to claim 31, wherein said first receiving mixer is provided so as to receive a local oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band.

33. (New) A semiconductor integrated circuit device according to claim 31, further comprising:

a first output pin electrically connected to said first low noise amplifier; and  
a second output pin electrically connected to said second low noise amplifier,  
wherein a radio frequency reception signal of the first frequency band amplified through said first low noise amplifier is outputted from said first output pin and a radio frequency reception signal of the second frequency band amplified through said second low noise amplifier is outputted from said second output pin.

34. (New) A semiconductor integrated circuit device according to claim 33, wherein said first receiving mixer is provided so as to receive a local oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band.

35. (New) A semiconductor integrated circuit device according to claim 33, wherein said first low noise amplifier comprises a first bipolar transistor having an emitter to which a ground voltage is to be applied, a base electrically connected to said first input pin, and a collector electrically connected to said first output pin, and

wherein said second low noise amplifier comprises a second bipolar transistor having an emitter to which a ground voltage is to be applied, a base electrically connected to said second input pin, and a collector electrically connected to said second output pin.

36. (New) A semiconductor integrated circuit device according to claim 35, wherein said first receiving mixer is provided so as to receive a local oscillation signal of the first frequency band and said second receiving mixer is provided so as to receive a local oscillation signal of the second frequency band.